KOZLOVSKIY, L.I., inzh.; KARNEYEV, N.A., inzh.

The KP-10-Z10 full-circle loading crane. Mekh.stroi. 15 no.12:
18 20 D 58. (MIRA 11:12)

(Cranes, derricks, etc.)

SHCHEFET EV, A.I., inzh.; KOZLOVSKIY, L.I., inzh.

Truck-mounted hydraulic hoist. Mekh.stroi. 16 no.2:15-17
F *59. (Hoisting machinery)

Cranes for mass housing construction. Stroi. i dor. mashinostr. 5 no.6:34-39 Je '60. (MIRA 13:7)

(Cranes, derricks, etc.)

KOZLOVSKIY, L.I., inzh.; KARNEYEV, N.A., inzh.

MSK-8-20 new mobile tower crane. Stroi.i dor.mash. 6 no.8:9-12
Ag '61. (Cranes, derricks, etc.)

VESELOV, A.A., inzh.; KARNEYEV, N.A., inzh.; KOZLOVSKIY, L.I., inzh.; STEPANOV, A.I., inzh.; TUSHNYAKOV, M.D., inzh.; SHCHEPET'YEV, A.I., inzh.; VDOVENKO, Z.I., red. izd-va; YUDINA, L.A., red. izd-va; KASIMOV, D.Ya., tekhn. red.

[Hoisting and conveying equipment for assembly and specialized operations] Pod"emno-transportnoe oborudovanie dlia montazhnykh i spetsial'nykh rabot. Pod red. A.I.Shchepet'eva. Moskva, Gostroitzdat, 1962. 634 p. (MIRA 16:5) (Cranes, derricks, etc.) (Hoisting machinery)

KOZLOVSKIY, L.I.; TUSHNYAKOV, M.D.; STEPANOV, A.I.; KORNEYEV, N.A.; SMETANSKIY, F.V.; SHEPET YEV, A.I., red.; SPIVAK, S.V., nauchnyy red.; LOGINOVA, R.A., red.; KOGAN, F.L., tekhn.

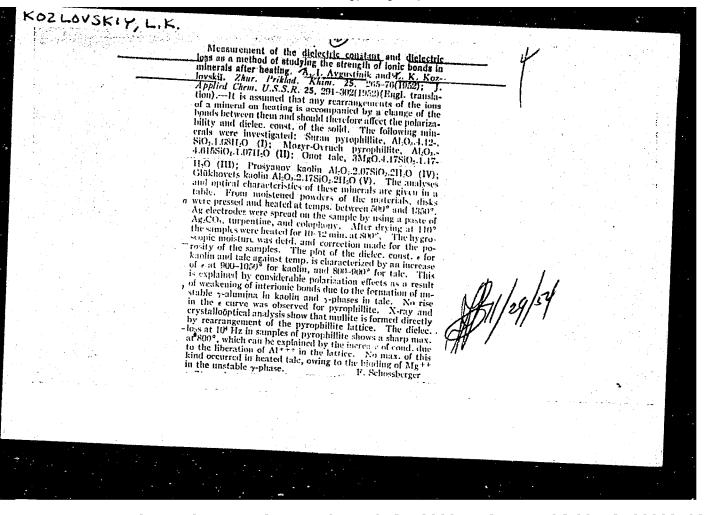
[Hoisting, conveying, and special machinery for building and repair work] Pod memno-transportnye i spetsial nye mashiny dlia stroitel nykh i montazhnykh rabot; katalog spravochnik. Pod red.A.I.Shepet'eva. Moskva, No.2.[Crauler cranes] Krany na gusenichnom khodu. 1963. 226 p. (MIRA 16:8)

1. TSentral'nyy institut nauchno-tekhnicheskoy informatsii po avtomatizatsii i mashinostroyeniyu.

(Cranes, derricks, etc.)

VESELOV, A.A., inzh.; KARNEYEV, N.A., inzh.; KOZLOVSKIY, L.I., inzh.; STEPANOV, A.I., inzh.; TUSHNYAKOV, M.D., inzh.; SHCHEPET'YEV, A.I., inzh.; VOLNYANSKIY, A.K., glav. red.; SUDAKOV, G.G., zam. glav. red.; TARAN, V.D., red.; SEREBRENNIKOV, S.S., red.; MIKHAYLOV, K.A., red.; STAROVEROV, I.G., red.; VOLODIN, V.Ye., red.; NIKOLAYEVSKIY, Ye.Ya., red.

[Hoisting and conveying equipment for assembly and specialized operations] Pod"emno-transportnoe oborudovanie dlia montazhnykh i spetsial'nykh rabot. Izd.2., dop. Moskva, Stroiizdat, 1964. 679 p. (MIRA 18:4)



PAVLOVA, Zinaida Pavlovna, 1918-, carpenter; akhanika, Valentina Ivanovna, 1908-, carpenter; KOZLOVSKIY, L.M., carpenter.

[Assemblage of wooden panels for partitions and subflooring. Experience of stakhanovite carpenters Z.P.Pavlova, V.I.Akhanina and L.M.Kozlovskii] Sborka dereviannykh shchitov dlia peregorodok i nakata; opyt stakhanovtsev-plotnikov Z.P.Pavlovoi, V.I.Akhaninoi i L.M.Kozlovskogo. Moskva, 1952. 13 p.

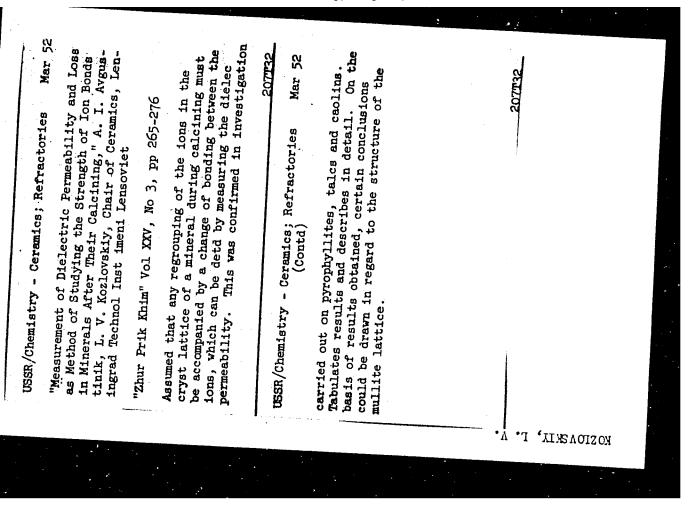
(MLRA 6:7)

1. Moscow. Vsesovuznaya tsentral'naya normativno-issledovatel'skaya stantsiya.

2. Trest Minmashstroya, g. Nikolayev (for Kozlovskiy).

3. Ves'yegonskiy de-revoobdelochnyy kombinat (for Pavlova and Akhanina).

(Carpentry)



KOZLOVSKIY, L.V.

USSR/Chemical Technology. Chemical Products and Their

I-9

Application - Silicates. Glass. Ceramics. Binders.

Abs Jour

: Referat Zhur - Khimiya, No 4, 1957, 12509

Author

Avgustinik A.I., Kozlovskiy L.V.

Title

Concerning the Strength of Ionic in Pyrophyllite After

Calcining

Orig Pub

: Zh. prikl. khimii., 1956, 29, No 7, 1035-1040

Abstract

Investigated was the strength of bonds between Al ions and Si ions in pyrophyllite of Mozyr'ovruch deposit, calcined at different temperatures, by the method of chemical treatment (solutions of alkalies and acids). It was found that on action of a 6% solution of HCl on samples of pyrophyllite calcined at different temperatures, the solubility of the sample calcined at 800° was highest amounting to 3.60 - 3.83% on the basis of the calcined material (slight solubility of Al₂O₃ is due to the "closed" structure of pyrophyllite block).

Card 1/2

- 61 -

USSR/Chemical Technology. Chemical Products and Their I-9
Application - Silicates. Glass. Ceramics. Binders.

Abs Jour : Referat Zhur - Khimiya, No 4, 1957, 12509

On treatment of calcined samples of pyrophyllite with 10% solution of KOH, greatest solubility of silica is found in samples calcined at 1100°. This is due to maximal weakening of Si-O-Si bonds in the crystal lattice of pyrophyllite. Weakening of bonds between ions in the crystal lattice of pyrophyllite provides conditions for a rearrangement of the pyrophyllite lattice into crystalline phases that are more stable at high temperatures (mullite, cristobalite).

Card 2/2

- 62 -

KOZLOVSKIY,

AUTHORS:

Avgustinik, A.I., Kozlovskiy, L.V., Konovalov, P.F.

76-11-18/35

TITLE:

On the Behavior of Muscovite When Heated (K voprosu ob otnoshenii

muskovita k nagrevaniyu)

PERIODICAL:

Zhurnal Fizicheskoy Khimii, 1957, Vol.31, Nr 11, pp. 2495-2500 (USSR)

ABSTRACT:

Here Karelian muscovite with a comparatively high heat- and chemical resistance was investigated. Its chemical composition was as follows: $SiO_2 - 44.80$, $TiO_2 - 0.25$, $Al_2O_3 - 35.54$, $Fe_2O_3 - 3.05$, CaO - 0.32, MgO - 1.37, $Na_{2}O - 1.58$, $K_{2}O - 8.82$, losses by annealing - 4.70%. Individual rutile- and chlorite crystals were admixed. The following is shown: 1.) Separation of water in muscovite dehydration takes place in two stages: up to 400-450° 10 - 12%, and in the interval between 600 and 9000 the most essential part is separated, which is constitutionally connected with the muscovite crystal lattice. 2.) Expansion of the sample, which is produced from finely ground muscovite, also takes place in two stages: a) at 400° (about 2% of the initial length), b) at 850-900° (about 1.7% of the initial length), which can be brought into connection with the separation of water in this stage. 3.) The action of a 6% hydrochloric acid solution upon the muscovite, which

Card 1/2

was annealed at different temperatures, proves the existence of an

On the Behavior of Muscovite When Heated

76-11-18/35

optimum of solubility of the pure clay component of the muscovite at 800° C because of a considerable weakening of the inter-ion linkages at this temperature. The absolute quantity of R203-oxides passing over into the solution is, however, not large. This is connected with the closed structure of the muscovite lattice packet. 4.) Judging from the refraction indices of the muscovite annealed at 1000° C, an isotropic substance, and with 1100° C a new crystal phase with Ng=1.540 and Np=1.536 occur. 5.) The data of the structural analysis prove that, up to a temperature of 1000°C, the muscovite lattice undergoes no change, but that it is completely destroyed beyond 1100°C, and that a phase 0 -K20.Al203.2SiO2, which, at a temperature of 1300° C decomposes into corundum, "mullite" and glass, is formed. There are 3 figures, 2 tables, and 20 references, 12 of which are Slavic.

ASSOCIATION: Institute for Technology imeni Lensovet, Leningrad (Tekhnologicheskiy institut im. Lensoveta, Leningrad)

SUBMITTED:

July 23, 1956

AVAILABLE:

Library of Congress

Card 2/2

83493

15.2210

S/081/60/000/013(I)/011/014 A006/A001

Translation from: Referativnyy zhurnal, Khimiya, 1960, No. 13(I), p. 448, # 53450

AUTHORS:

Avgustinik, A. I., Kozlovskiy, L. Y.

TITLE:

The Manufacture of Aluminum Oxide Protective Fixtures for High-Temperature Plunging Thermocouples by Plastic Forming and Casting Into Gypsum Molds

PERIODICAL: Tr. Leningr. tekhnol. in-ta im. Lensoveta, 1959, No. 57, pp. 15-19

TEXT: The author investigated problems of recrystallization sintering of Al₂O₃ by introducing into the composition a small amount of fine and superfine grained mineralizers. They studied vibromilling of commercial Al₂O₃ and preparation of protective jackets for plunging thermocouples up to 500 mm length in the capacity of internal fixtures of high-temperature plunging thermocouples with cermet tips for measuring temperatures up to 1,600-1,650 °C. It is established that in the vibromilling of commercial Al₂O₃ for 5-6 hours, the yield of particles of < 2 \mu size is 60 to 70% in dry milling and 90% in wet milling. Pure Al₂O₃ pipes are manufactured by the method of plastic forming

Card 1/2

83493

S/081/60/000/013(I)/011/014 A006/A001

The Manufacture of Aluminum Oxide Protective Fixtures for High-Temperature Plunging Thermocouples by Plastic Forming and Casting Into Gypsum Molds

with addition of an 18 - 20% solution of polyvinyl alcohol as plasticizer or by casting alumina dross of 33% moisture and 3.3 pH. The pipes are roasted after drying, first to 1,200 - 1,250°C and then to 1,600 - 1,650°C.

From the authors' summary.

Translator's note: This is the full translation of the original Russian abstract.

Card 2/2

L 06295-67 ENT(m)/EMP(e)/EMP(t)/ETI IJP(c) AT/WH/JD/JG/GD ACC NR: AT6027151 SOURCE CODE: UR/0000/65/000/000/0241/0244 AUTHOR: Avgustinik, A. I.; Golikova, O. A.; Klimashin, G. M.; Kozlovskiy, Neshpor, V. S. ORG: none TITLE: Dependence of certain electrophysical properties of titanium monocarbide on the carbon content SOURCE: AN SSSR. Otdeleniye obshchey i tekhnicheskoy khimii. Issledovaniya v oblasti khimii silikatov i okislov (Studies in the field of chemistry of silicates and oxides). Moscow, Izd-vo Nauka, 1965, 241-244 TOPIC TAGS: titanium compound, carbide, Hall constant, Hall mobility, conduction electron, resistivity, carbon ABSTRACT: The dependence of the resistivity ρ , thermal emf α and Hall constant R of titanium monocarbides on the carbon content was studied in the region of homogeneity on samples prepared from powdered Ti and acetylene black at 1750°. All the samples showed a negative Hall constant, indicating an n-type conductivity; the absolute value of R decreases rapidly with decreasing carbon content, indicating an increase in the concentration of free conduction electrons. The absolute differential thermal emf also decreases with diminishing carbon content. The resistivity decreases with decreasing carbon content in monocarbide phases TiCx, this being in accord with the in-1/2 Card

"APPROVED FOR RELEASE: Monday, July 31, 2000 CIA-RDP86-00513R000825920

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L 06296-67 EWT(m)/EWP(e)/EWP(t)/ETI LJP(c) AT/WH/JD/JG/GD
ACC NR: AT6027152 (A) SOURCE CODE: UR/0000/65/000/000/0244/0250
AUTHOR: Avgustinik, A. I.; Golikova, O. A.; Klimashin, G. M.; Kozlovskiy, L. V.
ORG: none $\frac{32}{12}$
TITIE: Effect of oxygen on certain properties of titanium carbide
SOURCE: AN SSSR. Otdeleniye obshchey i tekhnicheskoy khimii. Issledovaniya v oblasti khimii silikatov i okislov (Studies in the field of chemistry of silicates and oxides). Moscow, Izd-vo Nauka, 1965, 244-250
TOPIC TAGS: titanium compound, carbide, oxygen impurity
ABSTRACT: In a study of alloys of the TiC-TiO-Ti system, x-ray structural data showed that the contamination of TiC _x with oxygen causes a decrease in the size of the unit cell, this effect being more pronounced the closer the composition is to the stoichiometric proportion of TiC _x . This along with the influence of vacancies accounts for the great scatter of results obtained by various authors in their study of the lattice parameter of TiC _{1.0} . The melting point and microhardness of titanium carbide contaminated with oxygen decrease with increasing number of defects in the lattice, and to a lesser degree depend on the kind of metalloid atoms. As the oxygen content rises, the microbrittleness decreases at first, then begins to increase because of increasing ionic bond character. The electron concentration in tits time carbide containing some oxygen is influenced by two effects: when the number of vacancies in the metalloid Cord 1/2

L 06296-67

ACC NR: AT6027152

sublattice (i. e., the number of conduction electrons) is small, the current carrier concentration grows, since oxygen atoms give up to the conduction band their excess electrons relative to carbon. When the number of vacancies in the metalloid sublattice is large, the oxygen atoms do not give up their electrons, and oxygen in its reaction with titanium ties up the titanium electrons, causing a drop in the carrier concentration. Titanium carbide containing an oxygen admixture shows a metallic temperature dependence of the resistivity and thermal emf. The mobility of electrons at T = const drops with their increasing concentration and is relatively insensitive to the concentration of defects in the metalloid sublattice. The predominant scattering mechanism appears to involve scattering by lattice vibrations, and the energy dependence of the relaxation time is close to that observed in semiconductors. Orig. art. has: 13 figures.

SUB CODE: 07/ SUBM DATE: 09Apr65/ ORIG REF: 009/ OTH REF: 003

Card 2/2 gd

20321-66 EWT(m)/EWP(t)_IJP(c)_JD ACCESSION NR: AP5018912 UR/0363/65/001/006/0830/0834 546.821'261 12 AUTHOR: Avgustinik, A. I.; Klimashin, G. M.; Kozlovskiy, L. V. TITLE: Investigation of conditions of synthesizing pure titanium carbide by SOURCE: AN SSSR. Izvestiya. Neorganicheskiye materialy, v. 1, no. 6, 1965, 830-834 TOPIC TAGS: carbide, titanium carbide, titanium carbide synthesis ABSTRACT: An attempt has been made to synthesize high-purity titanium carbide by sintering a mixture of carbon black with 99.98%-pure titanium dioxide, 99.87%-pure electrolytic titanium or 99.98%-pure titanium. The mixture of components was vacuum sintered at 1570—2270K. Optimum results were obtained from a mixture containing 99.98%-pure titanium in an amount exceeding the stoic liometric by 7.5-10%, to compensate the loss of titanium by evaporation. Sintering of this mixture at 2020K yielded high-purity titanium carbide which contained 20% combined carbon and had a crystal lattice parameter of 4.3281 A. Oxygen in the initial material reduces

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Card 1/2

CIA-RDP86-00513R0008259200

"APPROVED FOR RELEASE: Monday, July 31, 2000 CIA-RDP86-00513R000825920

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BMITTED: 13Mar65	ENCL: 00	SUB CODE: MM, SS
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10. 2일	/EWP(t)/EWP(k)/EWP(z)/EWP(b) IJP(c) JD SOURCE CODE: UR/0181/65/007/009/2860/2862	
AUTHOR: Golikova. O. A.: Avgust	innik, A. I.: Klimashin, G. M.; Kozlovskiv, L. V.	1
ORG: Institute of	V9.55 Klimashin, G. M.; Kozlovskiv, L. V.	,0
grad Technological Institute im-	AN SSSR (Institut poluprovodníkov AN SSSR); Lenin Lensovet (Leningradskiy tekhnologicheskiy institut	P
TITUS: PI-A-	19,55 (Leningradskiy tekhnologicheskiy institut	-
Lobertias of	titanium carbide	
SOURCE: Fizika tverdogo tela, v.	27	
TOPIC TAGS: 01-2/, 44,55	7, 40. 3, 1965, 2860-2862	
thermoelectromotive force, Fermi	itanium compound, carbide, energy band structure,	
BSTRACT: The author	[4 경화] 공원 (1 2 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	
tion of carbon concentration. The	electrical properties of titanium carbide as a func data are used as a basis for an explanation of the	
esistivity thannal	ponsible for scattening of	8
of TiC _x $(x = 0.43-1.0)$. Powden me	force and Hall constant were measured in speciment	
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on concentrations, mobilities	ange for various values of x. Hall concentrations and effective masses are tabulated for various carthat the effective mass decreases with various car-	
was found	and effective masses are tabulated for various car- that the effective mass decreases with an increase	•
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L 9244-66 ACC NR. AF5022743 in concentration. It is assumed that the Ti-C bond is basic in stoichiometric TiC and that the Ti-Ti bond is strongly screened. The Ti-Ti bond becomes more and more important as the carbon content in the compound is increased. The stronger this conduction becomes, the wider the conduction band and the greater the deviation from semi-peratures is explained by assuming that the "metal" conduction band overlaps the higher conduction band of stoichiometric titanium carbide. At high temperatures, the Fermi level falls into the higher band and thermoelectromotive force begins to increase more rapidly. This hypothesis is confirmed by a(T) curves. Orig. art. has: SUB CODE: 20/ SUBM DATE: 14Apr65/ ORIG REF: 003/ OTH REF: 002

	AP6000898	Source (ODE: UR/0181/6	5/007/012/3698/3	7001
AUTHORS: Kozlovsk	0011kova, 0 1v. I. V.; (. A.; Avgusti Ordan'yan, S.	nnik, A. I.; K S.; Snetkova	limashin, G. M.;	
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OURCE:	Fizika tverdo	go tela, v. 7	no. 12, 1965.	<i>27</i> 3698-3700	
arbide,	S: titanium thermal emf,	compound, ziro Hall constant,	conium carbide, resistivity, t	hafnium compound	
ric prop	The purpose	of the invest	igation was to	compare the ale	2
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ACC NR: AP6000898

quantities against the carbon concentration are approximately the same for all three carbides. This demonstrates that the scattering mechanism and energy spectrum of the carriers are the same in all the compounds. An unexpected result is the fact that the effective masses of the three carbides are qual, since their lattices have different lattice constants and the participating electrons come from different shells. From the fact that the ratio of the distances between the metal and carbide atoms (R) and the radii of the metallic atoms (r) is also constant for all carbides, it is concluded that the orbitals of the metal atoms overlap equally. This explains the equality of the effective masses. The carrier scattering mechanism is briefly discussed. Orig. art. has: 2 figures, 1 formula, and 1 table.

SUB CODE: 07 / SUBM DATE: 23Ju165/ ORIG REF: 004/ OTH REF: 003/

Card 2/2

L 07823-67 -67 EWP(a)/EWT(m)/EWP(t)/ETI/EWP(k) IJP(c) JD/WW/JG/WR AP6034204 (// SOURCE CODE: UR/0153/66/009/004/0528/0532 ACC NRI AUTHOR: Avgustinik, A. I.; Kozlovskiy, L. V.; Klimashin, G. M. ORG: Department of Chemistry and the Technology of Fine Tachnical Ceramics, Leningrad Technological Institute im. Lensovet (Kafedra khimii i tekhnologii tonkoy tekhnicheskoy keramiki, Leningradskiy tekhnologicheskiy institut) TITLE: High-temperature reactions between titanium carbide and certain dasbixo SOURCE: IVUZ. Khimiya i khimicheskaya tekhnologiya, v. 9, no. 4, 1966, 528-532 TOPIC TAGS: titanium carbide, refractory oxide, zirconia, hafnium oxide, thoria, beryllia, high temperature ceramic material ABSTRACT: A discrepancy between calculated and experimental 7 temperatures of titanium carbide reactions with refractory Zroz, Hfoz, Thoz, and BeO led to a study of the reaction products which were obtained by sintering at 1770-2470K in vacuum the compacted mixtures of pure Tic with 10-80 wt. % of one of the refractory oxides. 27 Weight loss, shrinkage, density, and porosity of the sintered samples were measured and the effects of the sintering temperature and the oxide content in UDC: 546.821+546.261

L 07823-67 ACC NR: AP6034204 the starting mixture were evaluated. The data obtained, the lattice parameter data obtained by x-ray phase analysis, and the micrographs made it possible to establish in each case the mechanism of reactions and the phase formation. As a general rule, formation of TiC-base solid solutions with interstitial atoms of the second metal occurs in the presence of a large excess of the oxide and a titanium oxycarbide and metal form in the case of deficiency of the oxide in the starting mixture. Evolution of CO was detected in all cases. The formation of Be2C was detected by x-ray analysis in the reaction of TiC with 80% BaO. Complex oxycarbide solid solutions were formed in the reactions of TiC with 50% ZrO2 or HfO2 [sic]. ThO2 was found to be the least reactive of all the oxides studied, in agreement with theory. The reaction of TiC with 50% ThO2 at 2470K yielded a spongy surface phase of ThCx. Orig. art. has: 3 figures, 1 table, and 3 formulas. SUB CODE: 11/ SUBM DATE: 120ct64/ ORIG REF: 010/ ATD PRESS: Card 2/2

"APPROVED FOR RELEASE: Monday, July 31, 2000 CIA-RDP86-00513R000825920

	KOZICVSKIY, M.	
	"Spot Surface Hardening of Cast Iron" Stanki i Instrument, 10, No. 2, 1939. Engineer.	
1	Report U-1505, 4 Oct 1951.	
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	SO: Monthly List of Russian Accessions, Library of Congress, 1953, Uncl.	

"APPROVED FOR RELEASE: Monday, July 31, 2000 CIA-RDP86-00513R000825920

KOZLOVSKIY, M., inzhener-podpolkovnik; GAMULIN, A., inzhener-mayor, kand. tekhnicheskikh nauk

Reliability of rocket systems and time needed for preparation.

Av.i kosm. 44 no.4:74-77 *62. (MIRA 15:4)

(Guided missiles)

More than local peculiarities. Znan. ta pratsia no.4:28-30
Ap '59.

(Japan--Description and travel)

Edirut, a city of contrasts; a photosketch. Znan. ta pratsia no.5:26-27 My '60. (MIRA 13:10)

(Beirut.—Description)

KOZLOVSKIY, Ma, inzh.-podpolkovnik

Control equipment for air-to-air rockets. Av.1 kosm. 45 no.22
73-78 F '63. (MIRA 16:2)
(Guided missiles-Radar equipment)

KOZLOVSKIY, Mikola[Kozlovs'kyi, Mykola; TEPLITSKIY, K.[Teplyts'kyi,K.]

[In fraternal Bulgaria; journey with a camera]U bratnii BolgalIn fraternal Bulgaria; journey with a tamerajo bravill bosh rii; podorozh z fotoaparatom. Kyiv, Derzh.vyd-vo obrazotvor-choho mystetstva i muzychnoi lit-ry URSR, 1961. 6 p.

(MIRA 15:8)

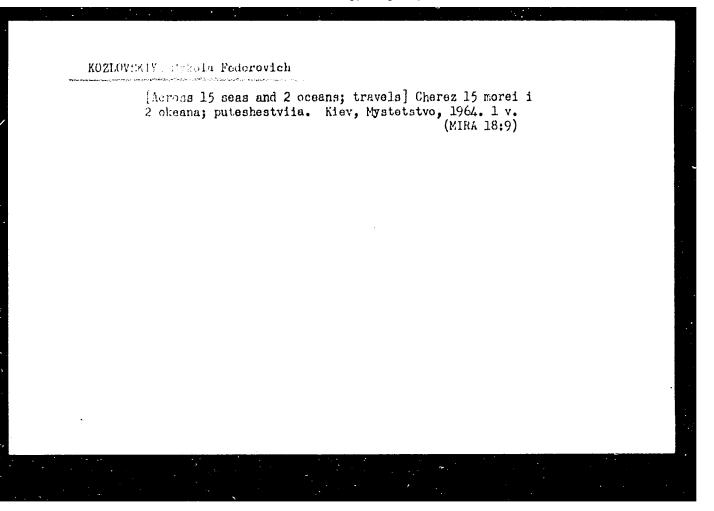
(Bulgaria--Views)

KOZLOVSKIY, M. [Kozlovs'kyi, M.]; POTAPSKAYA, I. [Potaps'ka, I.]

Sun loves this land. Znan.ta pratsia no.8:24-25 Ag '62.

(Capri—Description and travel)

(Messina—Description)



KOZLOVSKIY, M.

From all mainlands and continents. Inform.bivl. VDMEH no.1:45-46
Ja *65. (MIRA 18:3)

1. Zamestitel' nachal'nika inostrannogo otdela Vystavki dostizheniy narodnogo khozyaystva SSSR.

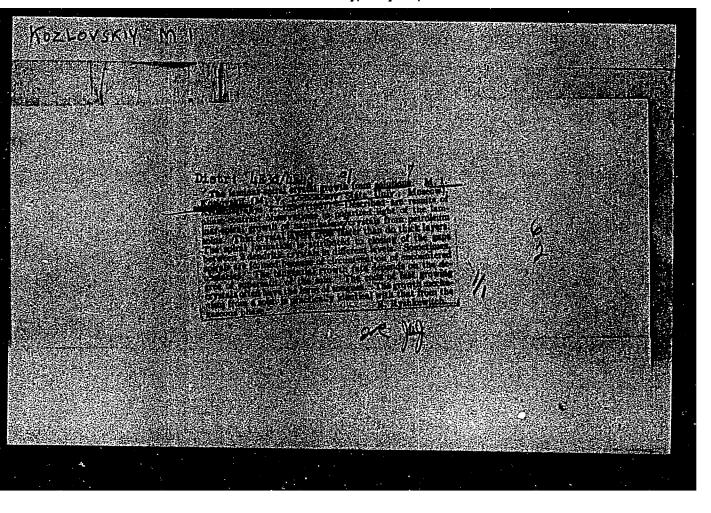
BESHKETO, V.K.; KOZLOVSKIY, M.G.; KUPRIN, V.A.; FLEYSHMAN, V.A.; MALAKHOV, K.N., inzh., retsenzent; POTAPOV, V.P., inzh., red.; VOROB'YEVA, L.V., tekhn. red.

[Transportation service for industrial enterprises; from the experience of the West Siberian Railroad] Transportnoe obsluzhivanie promyshlemnykh predpriiatii; iz opyta Zapadno-Sibirskoi zheleznoi dorogi. Moskva, Transport, 1964. 86 p. (MIRA 17:1)

Mechanization of labor consuming operations in the mines of Ordzhonikidzeugol' Trust. Ugol' 36 no.8:38-43 Ag'61.

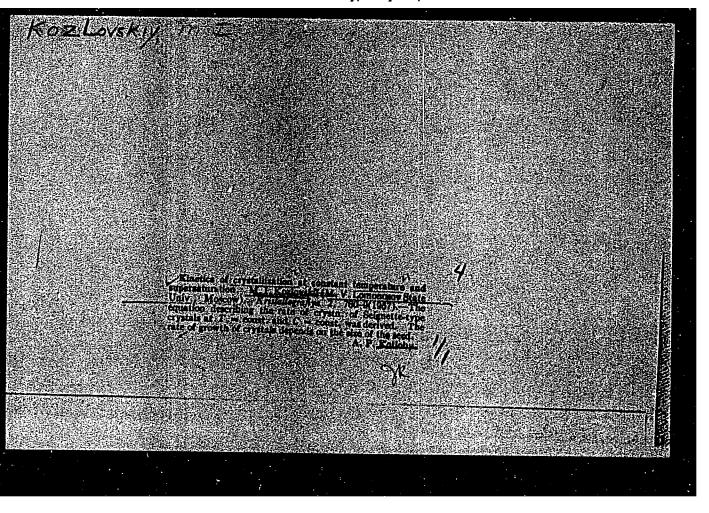
1. Trest Ordzhonikidzeugol'.

(Donets Basin--Coal mining machinery)



KCZLCVSKIY, F. I., Cand Phys-Math Sci--(diss) "Experimental study of the growth of crystals from solutions in the light of the theory of displacations." Los, Publishing House of the Acad of Sci USSR, 1953. 15 pp with graphs (Los State U in H.V. Lomonocov. Phys F culty. Chair of Crystallography), 130 copies (KL, 25-58, 107

-/5-



AUTHOR: Kozlovskiy, M.J.

70-3-2-12/26

TITLE:

The Formation of Screw Dislocations When a Crystal Grows over Solid Particles (Obrazovaniye vintovykh dislokatsiy pri obrastanii kristallom tverdykh chastits)

PERIODICAL: Kristallografiya, 1958, Vol 3, Nr 2, pp 209 - 213 (USSR).

ABSTRACT: It is experimentally shown that screw dislocations can be formed as a consequence of the inclusion of foreign particles in the process of the growth of crystals from solutions and from melts. It is established that not all foreign particles encountered by the growing crystal are included by it and that only part of the included particles cause the appearance of screw dislocations. The probability of the formation of screw dislocations on the inclusion of extraneous particles by a growing crystal is calculated.

Crystals of β-methyl-naphthalene were used (C₁₁H₁₀), growing from solution in ethyl alcohol in a closed cell on a microscope slide. This slide was fixed on the microscope stage attached to a water-circulating thermostat controlling the temperature to 0.01 °C. The temperature was lowered until crystals began to form; it was then raised a little so that almost all the Card 1/2

The Formation of Screw Dislocations When a Crystal Grows over Solid Particles

crystals re-dissolved. The temperature was then lowered slowly and the remainder were allowed to grow. Their progress was followed with a micro-cinematograph arrangement (38 frames per sec. at a magnification of 100). The thickening layers were visible because of the changing interference colours. Observation was through parallel Nicols. The illumination was oblique. Screw dislocations originating when the growing steps encountered foreign particles were successfully photographed. The fraction number of dislocations over number of foreign particles per mm (n/n) was plotted against the speed of growth in 80 p/sec.

There are 9 figures and 7 references, 5 of which are Soviet and 1 French, 1 English.

ASSOCIATION: Moskovskiy gosudarstvennyy universitet im. M.V. Lomonosova (Moscow State University imeni M.V. Lomonosov)

SUBMITTED: May 15, 1957 Card 2/2

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AUTHOR: Kozlovskiy, M.I.

70-3-2-21/26

TITLE:

The Formation of Screw Dislocations When Two Layers Growing on the Surface of a Crystal Meet (Obrazovaniye vintovykh dislokatsiy pri vstreche dvukh rasprostranyayushchikhsya po poverkhnosti kristalla sloyev)

PERIODICAL: Kristallografiya, 1958, Vol 3, Nr 2, pp 236 - 237 (USSR).

ABSTRACT: See paper by the same author - Kristallografiya, 1958, Vol 3, pp 209-213. The same substances and technique as in the previous paper were applied. It was observed that when two layers met a spiral was often generated, the rate of growth of which was given by the equation: $V_H = h_{st} V_{st}/y$ where V_H is the rate of growth of the crystal in the direction of the normal at the point of emergence of the axis of the screw dislocation and $V_H = h_{st} N$, h_{st} is the height of the step (Burgers vector), N is the number of new turns of the spiral appearing in unit time, $y = V_{st}t$ y being the distance between turns, V_{st} the rate of movement of the step and t the period of instantaneous rotation of the spiral at its centre Card 1/2

70-3-2-21/26 The Formation of Screw Dislocations When Two Layers Growing on the Surface of a Crystal Meet

> and N=1/t. Enlarged frames from the cine film taken through crossed Nicols of the growth process are reproduced. There are 1 figure and 6 references, 2 of which are Soviet, 3 English and 1 French.

ASSOCIATION:

Moskovskiy gosudarstvennyy universitet imeni M.V. Lomonosova (Moscow State University imeni M.V. Lomonosov)

SUBMITTED:

October 1, 1957.

Card 2/2

AUTHORS: Kozlovskiy, M.I. and Lemmleyn, G.G. 70-3-3-18/36 TITLE:

Investigation of the Layer-spiral Growth of Crystals of

β-methylnaphthalene, Growing from Solution in Ethyl Alcohol (Issledovaniye sloisto-spiral'nogo rosta kristallov

β-metilnaftalina, rastusĥchikh iz rastvora v etilovom spirte)

PERIODICAL: Kristallografiya, 1958, Vol 3, Nr 3, pp 351 - 357

ABSTRACT: For growth layers, growing tangentially on the OOl faces of crystals of β-methylnaphthalene from a solution in ethyl alcohol, the dependence of growth speed on super-saturation and on the layer thickness have been investigated. It was found that for small super-saturations, the growth of thick layers (at least 10-15 unit cell heights thick) predominates but that for large super-saturations the layers are only 1-10 unit cells thick. For the same substance, the dependence v(h) of velocity on thickness for growth from vapour and from the melt was studied and it was shown that the dependence is the same whether the growth is from vapour, solution or melt. The dependence of the distance between turns of the spirals on super-saturation and also the dependence of the magnitude of the period of rotation of the spiral on super-saturation were investigated. Card1/2 Observations were made using a thermostatted cell, the tempera-

70-3-3-18/36 Investigation of the Layer-spiral Growth of Crystals of β-methylnaphthalene, Growing from Solution in Ethyl Alcohol

> tures of the upper and lower faces being controlled separately, on the stage of a microscope. Changes in thickness were measured by observing interference colours and recording was by micro-cinematography. There are 9 figures and 8 references, 5 of which are Soviet and 3 English.

ASSOCIATION:

Moskovskiy gosudarstvennyy universitet im.

M.V. Lomonosova (Moscow State University imeni M.V. Lomonosov)

SUBMITTED:

December 27, 1957

Card 2/2

Kozlovskiy M. I. AUTHOR:

SOV/70-3-4-13/26

TITIE: On the Question of the Spiral Growth and Solution of Crystals (K voprosu o spiral'nom roste i rastvorenii

kristallov)

PERIODICAL: Kristallografiya, 1958, Vol 3, nr 4, pp 483-487 (USSR)

ABSTRACT: Using the microscope installation with cinematographic recording described earlier (Kristallografiya, 1958, Vol 3, pp 209 and 509), the transitional processes occurring between the spiral growth of crystals and their spiral solution and vice versa were examined. It was again confirmed that the solution spirals and the growth spirals are generated around the points of emergence of the axes of screw dislocations at the surface of the crystal and at the same centre the growth spiral has the opposite sign to the solution spiral. It has been shown that the process of transition from growth from solution to solution is qualitatively the same as the process of transition from growth from the vapour phase to evaporation. The particular material used was β -methylnaphthalene and growth on the OOl face was studied at 10 - 12 °C, where the solubility in ethyl alcohol is about 15 g/100 ml. The illumination was oblique and plane

Card 1/2

SOV/70-3-4-13/26

On the Question of the Spiral Growth and Solution of Crystals

polarised, half of the condenser being obscured by a knife edge. $n_z - n_x = 0.276$ and layers of 1 000 to 2 000 A

were readily visible. The growth and dissolution of crystals were recorded photographically at a speed up to 3 frames/sec (8 frames are reproduced) at which the temperature was changed. The spirals were of the usual Archimedean type.

The supersaturation and unsaturation were of the order of 0.1 °C. Acknowledgments to Prof. G.G. Lemmlein.

There are 2 figures and 10 references, 3 of which are Soviet and 7 English.

ASSOCIATION: Moskovskiy gosudarstvennyy universitet im.

M.V. Lomonosova (Moscow State University imeni M. V.

Lomonosov)

SUBMITTED: June 25, 1957

Card 2/2

AUTHOR: Kozlovskiy, M.I.

SOV/70-3-4-23/26

TITIE:

Apparatus for the Microsopic Examination of the Growth of Crystals from Solution (Ustanovka dlya mikroskopicheskogo issledovaniya rosta kristallov iz rastvorov)

PERIODICAL: Kristallografiya, 1958, Vol 3, Nr 4, pp 509-510 (USSR)

ABSTRACT: Parts of this apparatus have been described earlier (Kristallografiya, 1957, Vol 2, p 760 and 1958, Vol 3, p 209). A saturated solution is circulated by a pump through a glass cell on a microscope stage. The stock solution in the reservoir is in a thermostat and the paths of the solution are maintained at definite temperatures, the solution heater being in the return pipe. The lower side of the observation chamber has a cooling-water cell attached to it and the upper side of the cell is electrically heated. The main temperature measurements are made in the reservoir but a differential thermocouple of high accuracy (± 0.02 °C) measures the supersaturation of the solution under observation. To detect the point of saturation of a solution, use is made of the observation

Card 1/2

Apparatus for the Microscopic Examination of the Growth of Crystals from Solution

that when a crystal is not in equilibrium and is dissolving or crystallising currents of variable density can be seen round it with suitable illumination - the crystal, illuminated by parallel light, is projected onto a screen. The accuracy of such determinations is 0.1 - 0.05 °C. There are 2 figures and 3 Soviet references.

ASSOCIATION: Moskovskiy gosudarstvennyy universitet

im. M. V. Lomonoscva (Moscow State University

imeni M.v. Lomonosov)

SUBMITTED: June 25.

June 25, 1957

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L 18974-63

EWP(q)/EWT(m)/BDS

AFFTC/ASD

ACCESSION NR: AT3001913

S/2912/62/000/000/0193/0198

AUTHOR: Kozlovskiy, M. I.

TITLE: Spiral formations on Bi crystals

SOURCE: Kristallizatsiya i fazovyye perekhody. Minsk, Izd-vo AN BSSR,

1962, 193-198

TOPIC TAGS: crystal, crystallization, crystallography, trigonal, syngony, Bi,

spiral, growth, rhomboheder

ABSTRACT: The paper describes the mechanism of the formation of the 'skeletal spirals" observed in Bi crystals which, as is known, pertain to the trigonal syngony and which form rhomboheders differing very little from a cubic shape and are nearly square-faced (87°34'). The tendency of Bi crystals toward lamellar growth suggests their capability of forming spiral growths. The spiral formations illustrated in photographs exhibit a great step height and a great distance between coils in the spirals. For example, h=100-200 micron, y=200-500 micron. There are three types, depending on whether the center of the spiral is below the edge, coplanar with the edge, or above the edge. The dynamics of the spiral formation is explored experimentally. Fused Bi at 280-290°C was poured onto an inclined glass

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APPROVED FOR RELEASE: Monday, July 31, 2000

L 18974-63

ACCESSION NR: AT3001913

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plate (60-70° slope) held at 30-35°C temperature. Spirals formed without fail. Two hypotheses are possible: (1) The mechanism of their formation is analogous to that of the formation of ordinary dislocational spirals; (2) they form as a result of skeletal growth. The dislocational hypothesis is rejected. It is concluded that the spiral growth is of the skeletal type and appears to be a consequence of a non-uniform temperature-field distribution during the rapid cooling of the poured fusion. "The author takes this opportunity to express his cordial gratitude to G.G. Lemlein and A.A. Chernov for the valuable critical remarks and aid given to him in the selection of the correct explanation of the observed phenomenon." Orig. art.

ASSOCIATION: none

SUBMITTED:

DATE ACQ:

16Apr63

ENCL: (

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SUB CODE:

CH, PH, MA, EL

NO REF SOV:

001

OTHER: 002

Card 2/2

APPROVED FOR RELEASE: Monday, July 31, 2000

L 19753-63

ENT(1)/ENP(q)/ENT(m)/ENP(B)/BDS AFFTC/ASD/ESD-3/IJP(C)

ACCESSION NR: AT3001942

\$/2912/62/000/000/0404/0410

TITLE: On the effect of an electrical field on the rate of nucleation of crystall tion centers

SOURCE: Kristallizatsiya i fazovyye perckhody. Minsk, Izd-vo AN BSSR, 1962, 404-410

TOPIC TAGS: crystal, crystallization, crystallography, electrical, field, nucleation, center, supersaturation, field strength, NH4-

ABSTRACT: The paper describes an experimental investigation of the effect of an electrical field on the process of crystallization from supersaturated solutions of the salts NH4Cl, NH4Br, NH4I, NaCl, NaBr, NaF, KI, KCl, CdI2, NiSO4, and CuSO4. It was shown that the degree of the effect of an electrical field on the rate of nucleation of crystallization centers (CC) in supersaturated solutions depends on the crystallizing substance; more specifically, it was found that all of the salts tested, except for NiSO4 and CuSO4, experienced a significant acceleration of the appearance of new CC's in an electric field of 1-30,000 v/cm. In the solutions of NH4Cl and NH4Br, it was found that the mean rate of appearance of

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APPROVED FOR RELEASE: Monday, July 31, 2000

L 19753-63

ACCESSION NR: AT3001942

new CC's is directly proportional to the supersaturation and to the square of the existing electrical potential gradient. In the tests, a drop of the test substance was deposited on a glass base plate placed on a common platform between two metal plates, all of which are situated on a thermostatic microscope table. No physical or electrical contact existed between the metal plate and the drop. An electrical field of 0-50,000 v/cm was established between the two metal plates. At potential gradients of 30-35,000 v/cm an electrical discharge occurred between the two metal plates. The number of CC's was counted by photography, cinematography, and visually. The drop of test solution heated slightly above the saturation temperature (Tg) was injected under a layer of vaseline oil. Supersaturation was then achieved by cooling. Thereupon, a constant electrical field was established for 10-30 sec, and the CC's were counted. Numerous tests showed that NH4Cl not subjected to an electrical field gave rise to only a single CC and the growth of a single dendrite. The increased number of CC's appearing under the effect of an electrical field obeyed the afore-stated regularities as functions of the supersaturation and the field strength. In addition, the tests show that new GC's appear under the effect of an electrical field, even in a system that is isolated from the ambient T in the absence of microscopic dust particles of the crystallizing substance. An interesting phenomenon which, possibly, may aid in finding an explanation for the mechanism of the formation of CC's in an electrical field is the

Card 2/3

L 19753-63

ACCESSION NR: AT3001942

observed massive appearance of CC's following a condenser discharge through the droplet. The author attributes this effect to mechanical action. The tests performed here, as well as those described in the literature, are still inadequate to serve as a foundation for an exhaustive description of the mechanism of nucleation of new CC's in an electrical field in a supersaturated solution. Orig. art. has 6

ASSOCIATION: none

SUBMITTED: 00

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16Apr63

ENCL: 00

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SUB CODE:

CH, PH, MA

NO REF SOV:

008

OTHER: 000

Card 3/3

APPROVED FOR RELEASE: Monday, July 31, 2000

\$/070/62/007/001/022/022 E073/E335

AUTHOR:

Kozlovskiy, M.I.

TITLE:

On the influence of the electric field on the germina-

tion of crystallization centres

PERIODICAL: Kristallografiya, v.7. no.1, 1962, 157-159

TEXT: Applying a method proposed by A. V. Shubnikov, the author investigated the influence of a DC field on saturated solutions of salts of halogens and some sulphates. A drop of the investigated saturated solution was placed on a microscope slide and introduced between two metallic plates, which were glued onto the glass surface of the thermostat table of the microscope; there was no contact between the drop and the metal plates. A uniform electric field was applied to the plates, which could be varied within limits up to 30 kv/cm. The saturation temperature of the investigated salt solutions was 20°C and the microscope slide was at 35°C. Therefore, the drop of the solution was gradually heated up to $35\,^{\circ}\text{C}$ and evaporated. As a result the solution became supersaturated and crystals began to grow at the edges of the drop, It was found that the influence of the electric field was most Card 1/2

On the influence of the electric 3.5, 5/070/62/007/001/022/022E073/E335

pronounced on solutions of NH_LC1 and NH_LBr , for which no new centres formed inside the drop in the absence of an applied field, At a given temperature, the speed of formation of new centres of crystallization per unit of area of an investigated preparation was found to be directly proportional to the degree of saturation of the solution and the square of the voltage of the electric field, It obviously also depends thus: This dependence can be expressed thus: $v = k(c - c_0)E^2$ It obviously also depends on the substance being crystallized,

(1)

where k - proportionality coefficient; (c-c₁) - saturation; E - field strength. Photographs are included of four drops of the $\mathrm{NH_4Cl}$ solution which were subjected to the effect of electric fields of various strengths. There are 2 figures.

ASSOCIATION: Tiraspoliskiy gosudarstvennyy pedagogicheskiy institut im. T. G. Shevchenko (Tiraspol State

Pedagogical Institute imeni T. G. Shevchenko)

SUBMITTED: April 19, 1960 (initially)

March 11, 1961 (after revision)

Card 2/2

KOZLOVSKIY, M.I.

Formation of crystallization centers on the surface of aqueous solutions of electrolytes following a spark discharge. Rost krist. 4:27-31 '64. (MIRA 17:8)

KOZLOVSKIY, M.I.

Effect of a glowing electric discharge and impurities on spherulite formation in sulfur films during crystallization from the gaseous phase. Kristallografiia 10 no.1:125-128 Ja-F 165.

1. Tiraspol'skiy gosudarstvennyy pedagogicheskiy institut imeni Shevchenko.

PERSONNELS NOT (C)/EPT(C)VATE(S) = 110

Accession in the Actions for

UR/0070/65/010/000/05:4/05:15

AUTHORE KOZ GVEK V

PLANTS: Refect of a spare mischarde on the layer-spiral growin and evaporation of crystals (side the participation of drops of the bigging the plants)

SOURCE: XCASC:1102; 185.Var (V2.10) 100; 4; 1965; 534-538

TOPIC TAGS: Crystal growing Bischric discharge, organic crystal

ABSTRACT: As newspitenomenon — the appearance of a consideral communication of drops of the me t on the surface of a growing covered due to a spark discharge, we was investigated on crystals of β-methy nabrished lene \(\frac{\partial}{\partial} \) \(\

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APPROVED FOR RELEASE: Monday, July 31, 2000 CIA-R

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11 64559265 Accession nr: = AD5018722

Card 2/3

Used to keep the temperaturator archamber constant within 0.20. The discharge occurred between two steel needles inside the chamber. The temperature of the chamber was measured with copper-constant in thermocouples. A polarizing microscope was used and photographs were taken with ordinary and cine attachments. The discharge was produced by an induction so I with a mechanical interrupter supplied with 50-cycle AC current. It was observed that during a spark fishcharge close to crystals of certain organic compounds surrounded by their unsaturated vapor there appears on their surfaces a large number of displets of the mair depositing on the front of the steps and exhibiting the rine structure of planes and grain boundaries otherwise unnot ceable eventwiff the microscope. The times required for obtaining a complete picture of the plane of a growing crystal were investigated as a function of same of the discharge parameters and the distance of the discharge from the crystal. The behavior of the droplets and of the crystal or prolonging the discharge and after it ceases is described. Originary pass 5 figures and 3 photographs.

"APPROVED FOR RELEASE: Monday, July 31, 2000 CIA-RDP86-00513R000825920

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L 22092-66 EWT(1)/EWT(m)/EWP(t) IJP(c) JD ACC NR: AP6012942 SOURCE CODE: UR/0070/65/010/001/0125/0128 AUTHOR: Kozlovskiy, M. I. Tiraspol' State Pedagogical Institute (Tiraspol'skiy gosudarstvennyy pedinsti-21, 44, 55 TITLE: Effect of an electric glow discharge and impurities on the formation of spherolites in sulphur films during crystallization from the gas phase Kristallograflya, v. 10, no. 1, 1965, 125-128 TOPIC TAGS: sulfur, glow discharge, spherolite, crystallization, cadmium, zinc, aluminum ABSTRACT: A finely crystalline film is usually formed when sulphur is deposited from the gas phase at atmospheric or reduced pressure onto glass at room temperature. A different picture is observed if crystallization occurs in the presence of factors tending to form rhombic sulphur before it is deposited on the glass. Such factors are Cd, Zn, or Al vapor, or a glow discharge. The deposit on the substrate in this case consists of separate small crystals of sulphur, around which spherolites or plate-like crystals may grow. This is due to the fact, established by the authors, that the majority of the small crystals of rhombic sulphur are negatively charged. Evaporation with another substance or in the presence of a glow discharge gave almost all the forms of spherolites des-

ACC NR. AP6012942 | Cord 2/2 | Acc | Acc

KOZLOVSKIY, M.M., student I kursa

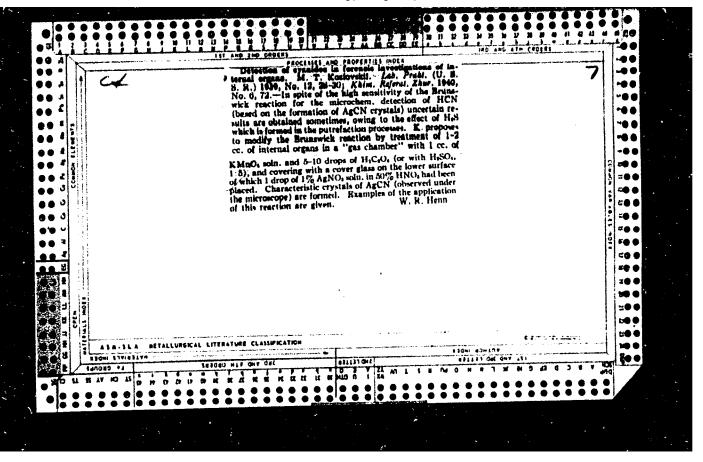
Secondary electron emission from Al₂0₃. Sbor.stud.nauch.rab. LEIS no.1:32-43 '59. (MIRA 13:4)

1. Leningradskiy elektrotekhnicheskiy institut svyazi imeni prof.M.A.Bonch-Bruyevicha. (Photoelectric multipliers) (Secondary---Electron emission)

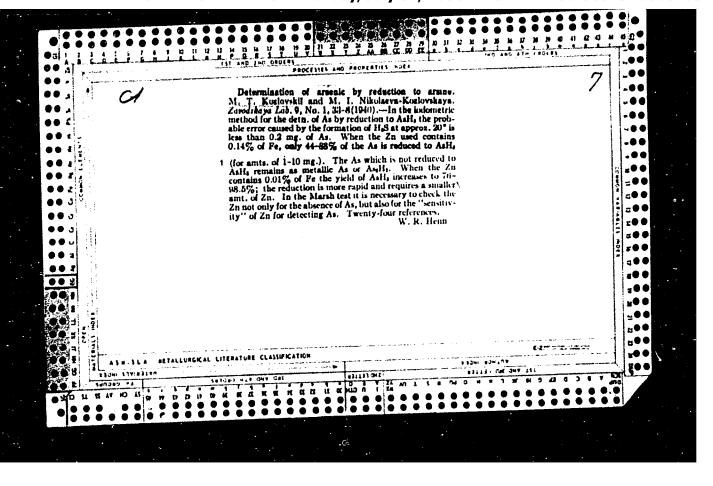
KOZLOVSKIY, Mikhail Timofeyevich; PETROV, Vyacheslav Vasil'yevich;
KHANIN, N.S., kand. tekhn. nauk, retsenzent; FEDOSEYEV, L.N.,
red.; DONSKAYA, G.D., tekhn. red.

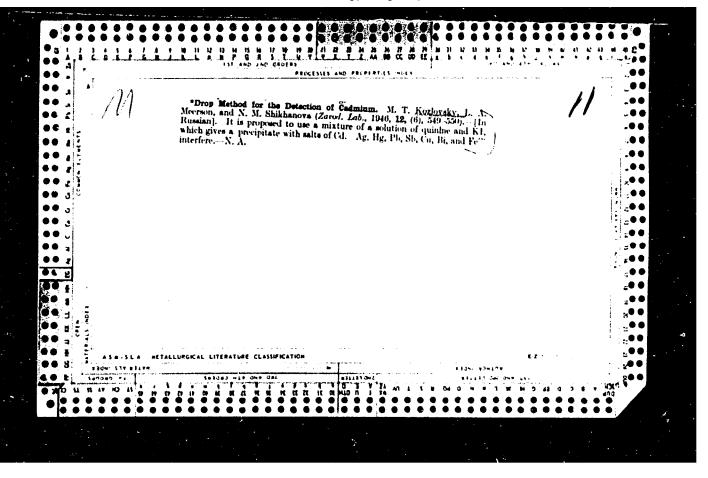
[Fuel equipment of IaAZ2-204 and IaAZ-206 diesel engines; design, maintenance and repair] Toplivnaia apparatura dizel'nykh dvigate-IaAZ-204 i IaAZ-206; konstruktsiia, obsluzhivanie i remont. Moskva, Nauchno-tekhn. izd-vo M-va avtomobil'nogo transp. i shosseinykh dorog RSFSR, 1961. 214 p. (MIRA 15:1) (Diesel engines)

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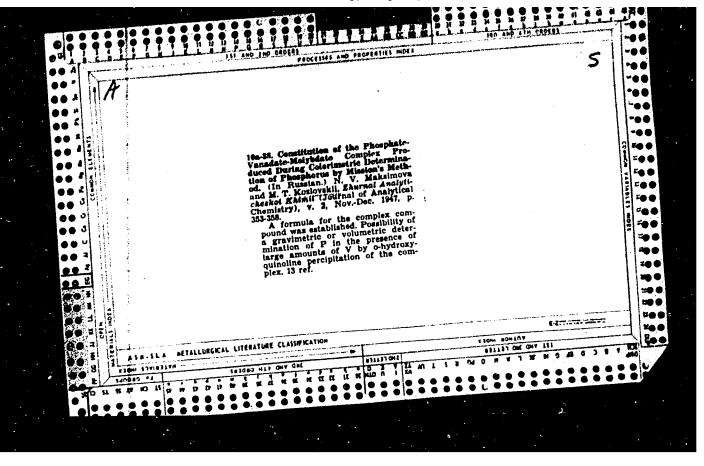


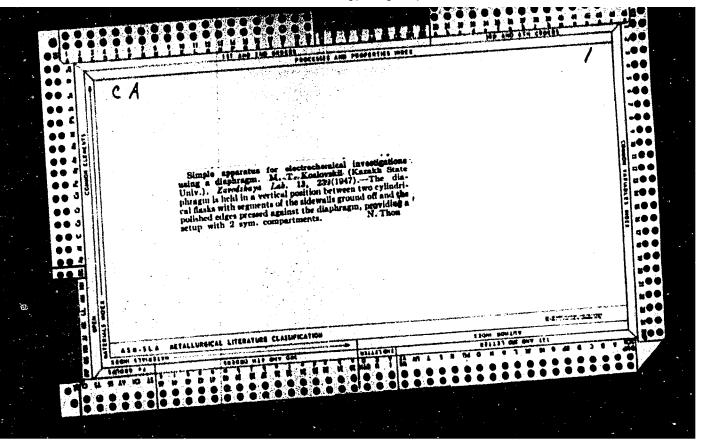
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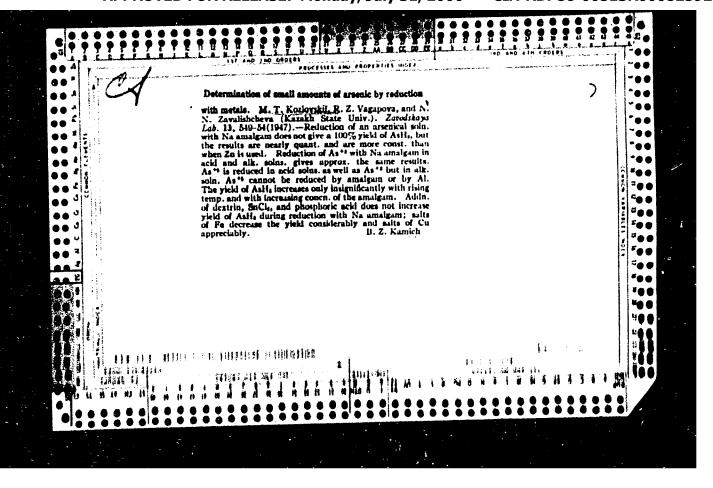


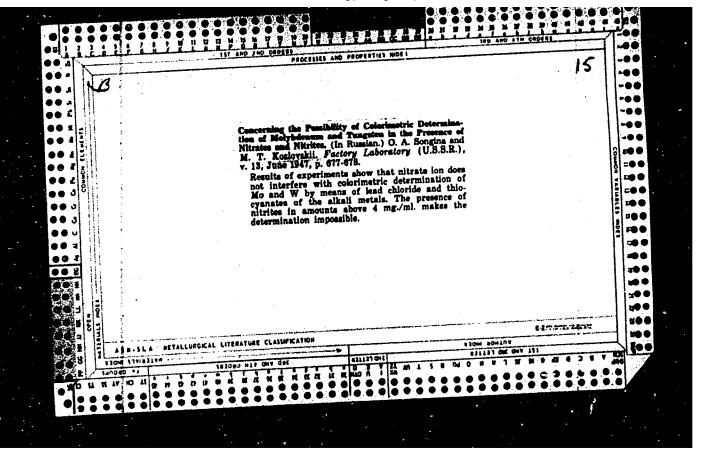


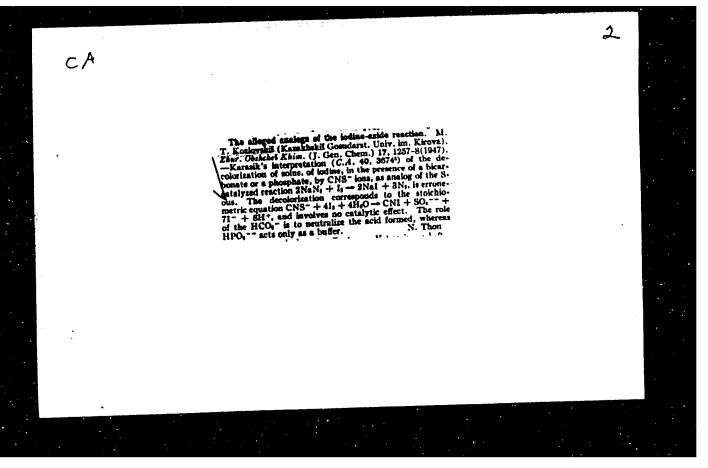
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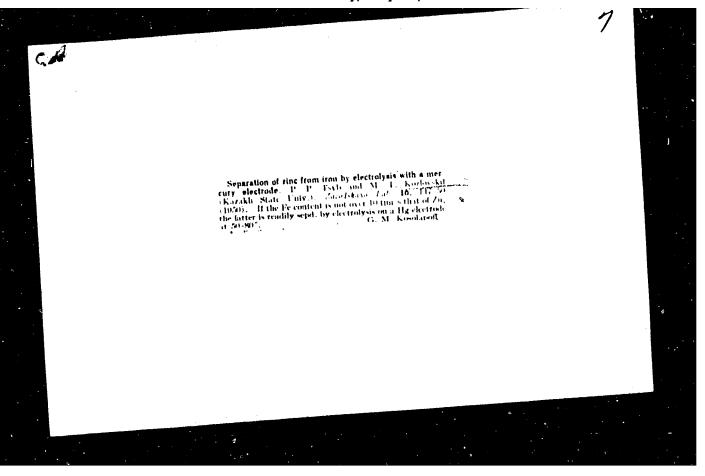


SONGINA, O.A.; VOYLOSHNIKOVA, A.P.; KOZLOVSKIY, M.T.

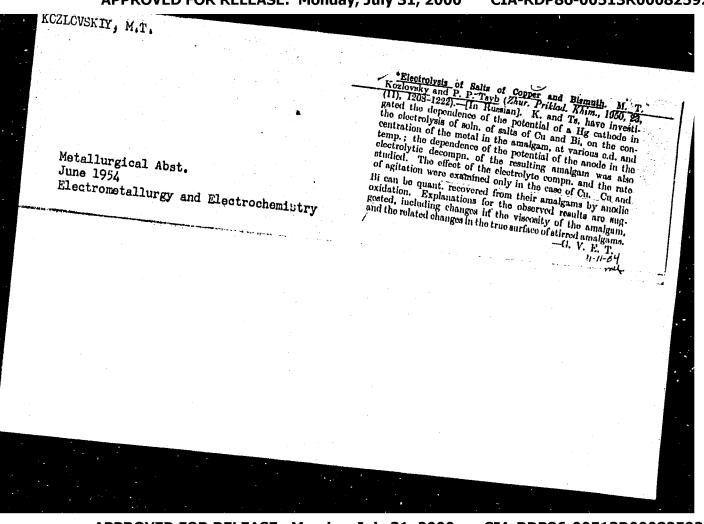
Amperometric titration. Part 1. Izv.AN Kazakh.SSR Ser.khim. no.3:
81-101 '49. (MLRA 9:8)

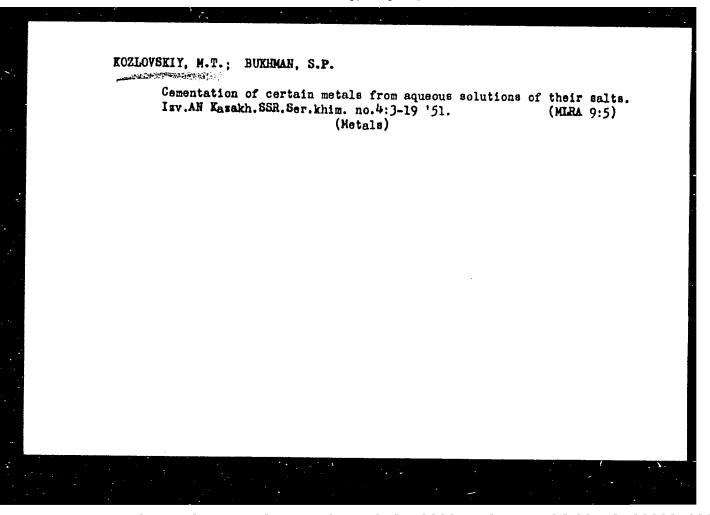
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"APPROVED FOR RELEASE: Monday, July 31, 2000 CIA-RDP86-00513R000825920



KOZLOVSKIY, M. T.	16077.1	USSR/Chemistry - Bismuth (Contd) way 50 usself to be sensitive than method with potassium iodide. Error of sensitive than may amount to up to 10%.	"Zavod Lab" Vol XVI, No > Attempts to establish possibilities for chronometric determination of small amounts of bismuth, e.g., to determination of small amounts of bismuth establish inverse proportionality between bismuth establish inverse proportionality between bismuth establish inverse proportionality between bismuth of solution. Quantity and time required for darkening of solution. Pinds chronometric determination of bismuth in quantities 0.0014-0.045 mg is approximately ten times more titles 0.0014-0.045 mg is approximately	USSR/Chemistry - Bismuth Analysis, Chronometric "Chronometric Method for Determination of Minimum "Chronometric Method for Determination of Minimum Quantities of Bismuth," M. T. Kozlovskiy, S. P. Gush- china, Inst of Chem, Kazakh Affiliate, Acad Sci USSR, 32 pp





SONGINA, O.A.; VOYLOSHNIKOVA, A.P.; KOZLOVSKIY, M.T.

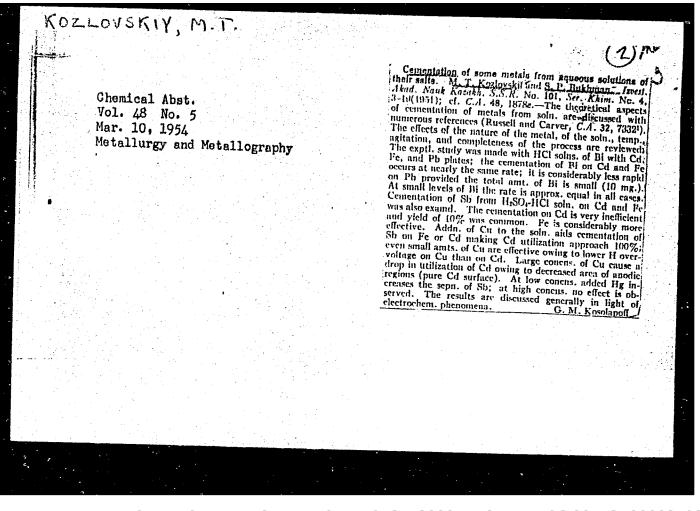
Amperometric titration. Part 2. Izv.AN Kazakh.SSR.Ser.khim. no.4:
80-89 '51.

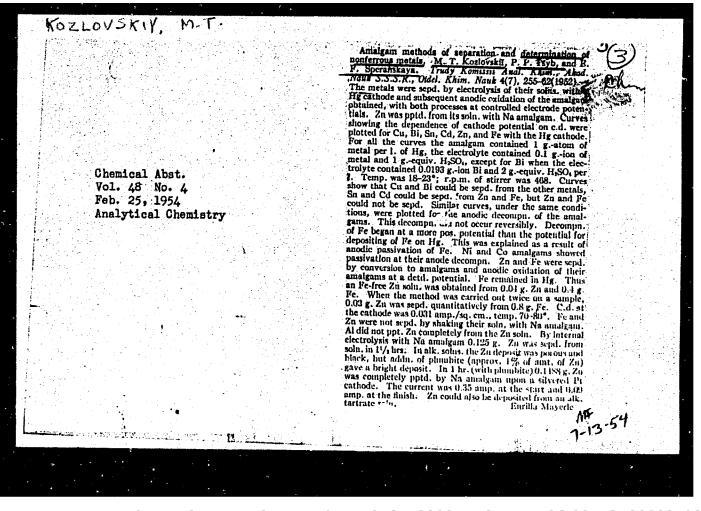
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(Conductometric analysis) (Copper) (Iron)

KOZLOVSKIY, M. T.		ligam due to changed metal cace of amalgam due to formatice affect cd and potentials.	nistry - Electrolytic Refining of Metals (Contd)	By examn of electrolytic deposition at anode and decompn at cathode of Sn and Cd amalgams, established dependence of cathode and anode potentials in respective cases at different temps and cd on (1) concn_of metals in amalgams, (2) concn of metal ions in electrolyte, (3) acidity of electrolyte (for Sn).	"Electrode Potentials in the Electrolysis of of Different Metals With a Mercury Electrode, Tayb, M. T. Kozlovskiy, Kazakh State U imeni S. M. Kirov "Zhur Prik Khim" vol XXIV, No 8, pp 840-850	USSR/Chemistry - Electrolytic Refining of Metals
	190128	• B C	Aug 51 Changed	established in respection concupor in election 190728	of Salts de," P. P. ni	Aug 51

KOZLOVSKIY, M.T.	190733	USSR/Chemistry - Electrolytic Refining of Aug 51 Metals (Contd) Metals (Contd) electrolyte, (3) rate of agitation. Almost total electrolytic transfer of Zn from amalgam to elec- trolyte is possible.	"Electrolysis of Zinc Salts," M. T. Kozlovskiy, P. P. Tsyb, Ye. I. Ruzina, Kazakh State U imeni g. P. P. Tsyb, Ye. I. Ruzina, Kazakh State U imeni g. P. P. Tsyb, Ye. I. Ruzina, Kazakh State U imeni g. P. P. Tsyb, Ye. I. Ruzina, Kazakh State U imeni g. M. Kirov "Zhur Prik Khim" Vol XXIV, No 8, pp 882-886 "Zhur Prik Khim" Vol XXIV, No 8, pp 882-886 "Zh electrolytic deposition of Zn on Hg cathode, and in electrolytic decompn of resultant amalgam at anode, established dependence of potentials of anode, established dependence of potentials of cathode and anode in respective cases on (1) concurs of Zn in amalgam, (2) concurs of Zn ions in	UBSER/Chemistry - Electrolytic Refining of Aug 51 Metals
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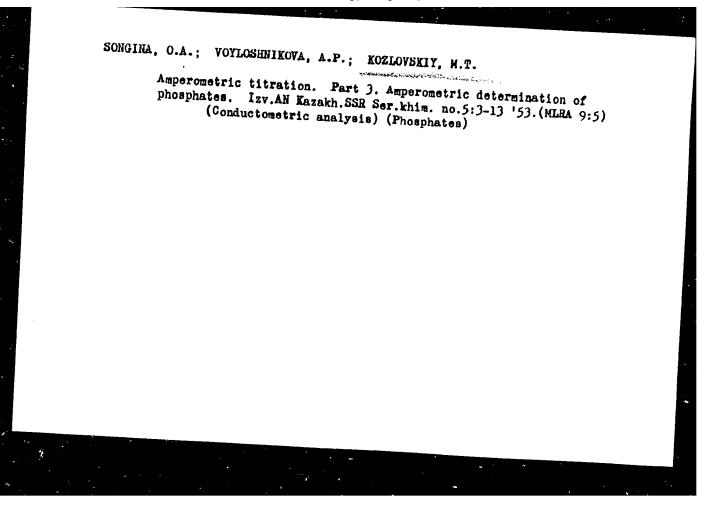
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√ 0	ZLOVSKIY, M.T.	mr y
	Chemical Abst. Vol. 48 No; 4 Feb. 25, 1954 Analytical Chemistry	Cementation as a method for separating metals. M. T. Kozlovskii, S. P. Bukhnian, and A. T. Malyuk. Trudy Komissii Anal. Khim., Akad. Nauk S.S.S.K., Uddi. Khim. Nauk 4(7), 263-73(1952).—Expts. on the cementation of Bi and Sb on Cd, Pe, and Pb, of Cd and Pb on Na amalgam, and of Cd on Zn amalgam are described. For the Bi and Sb expts. sheets of metal were placed in boiling HCl or HCl-
		(over)

H₂SO₄. For large conens, of Bi the rate of cementation depended on the potential of the cementing metal. For small conens, of Bi the rate depended on the diffusion rate of the Bi ions. When 10.0 mg, Bi in 100 ml, of soln, was treated with Cd, Fe, and Pb, 53, 12, and 95%, resp., of the amt, of metal added was used to ppt. Bi. The rest of the metal was used in forming H. In 25 min, 89, 85, and 70% of the Bi was sepd, by Cd, Fe, and Pb, resp. The reaction rate could not be calcd, exactly because the area of the electrode surfaces changes. When 1.00 mg. Bi in 100 ml, was treated with Cd, Fe, and Pb, 13, 1.4, and 0%, resp., of the metal added was used to ppt. Bi. In 25 min, 50, 70, and 0% of the Bi was sepd, by Cd, Fe, and Pb, resp. When 100 mg. Of Pb ion was added, 1 mg. Bi in 100 ml, was 98% sepd, on Cd, and no It was formed. Similarly in 25 min, 0.11 mg. Bi was 90% sepd, on Cd, and almost no Cd was used for H formation. Fifty mg. Sb was sepd, quantitatively on Cd when 20, 80, and 160 mg. Cu ion were added, with 90, 71, and 50%, resp., of the added Cd used for H formation. Cu formed a compid, with the Sb and raised the discharge potential of Sb ions. When Bb was cemented on Fe, Cu ion gave similar results. Expts, with annalgams were conducted in 100-ml, beakers at 20° with const, speed for the stirrer. These results were obtained for 0.1120 g. Cd after 20 min, of

treatment with Na amalgam. Cd alone was not sept. quantitatively on the Na amalgam. In neutral and in 0.1N acid solns, by addn. of 0.0651 g. Zn ion before addn. of Na amalgam 100% of the Cd was sepd., with 52.5 and 22.8% of the added Na used for Cd sepn. In neutral and 0.1N acid solns, with 0.0588 g. Ni ion 57.2 and 64.3% Cd, resp., was sepd., with 20 and 32%, resp., of the added Na used for Cd sepn. In neutral and 0.1N acid solns, with 0.0538 g. Fe ion 100% and 89% Cd, resp., was sepd. with 62.5 and 32.3%, resp., of the added Na used for Cd sepn. In neutral and 0.1N acid solns, with 0.0538 g. Cu ion 98.7 and 100% Cd, resp., was sepd. with 49.4 and 22.2%, resp., of the added Na used for Cd sepn. With Ni, chiefly Cd was comented first. In neutral soln, with Cd and Fe (or Cd and Ni) neither metal transferred completely to the 11g. In 0.1N acid both Cd and Cu transferred completely to the 11g. Other metals hindered Cd cementation on the Na amalgam. In acid soling amalgam sepd. Cd faster than Na amalgam. In acid soling gam had little effect on Ni and Fe. In alk soln., Pho could be sepd. quantitatively on Na amalgam, but 80% of the added Na was used for 11 fornation. Here 1% amalgams gave better results than 0.5% amalgams. With 1% Na amalgam were formed. Their approx. compn. was 11g 99, Ph 0.27, and Na 0.55%. Sn could not be constituted by Na amalgam in air.

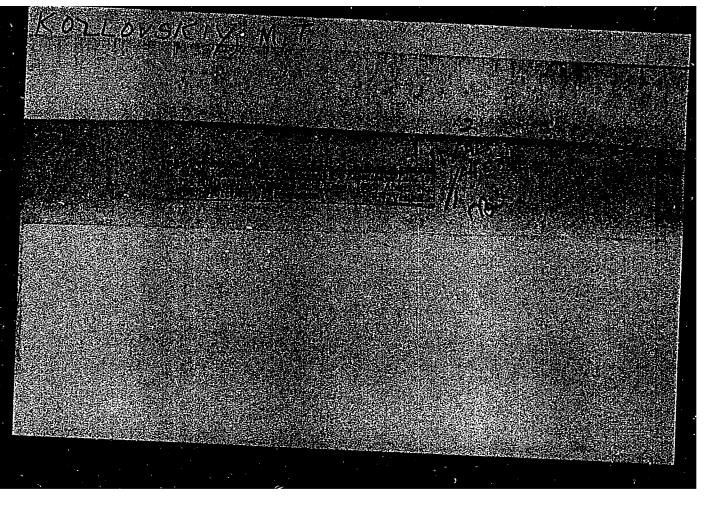


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Polarography of salts of various metals with the aid of amalgam electrodes. Izv.AN Kazakh.SSR Ser.khim. no.5:14-21 '53.

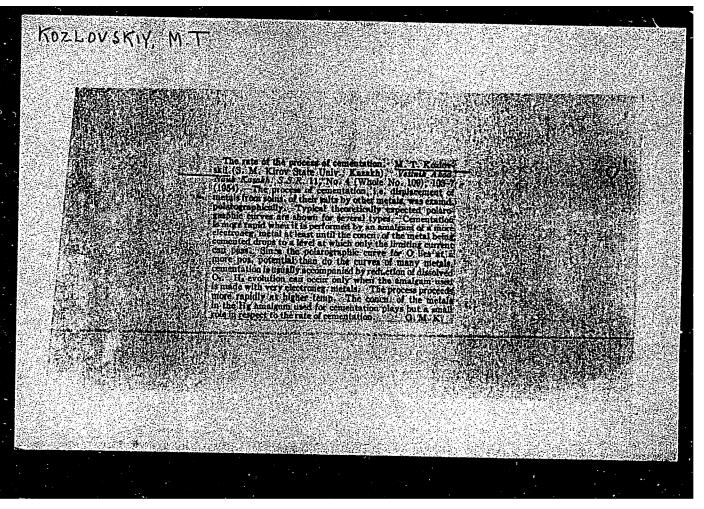
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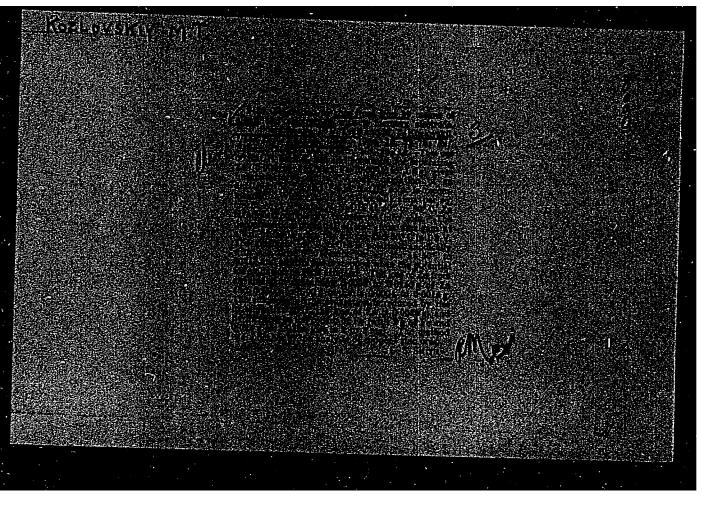
(Polarography) (Salts)



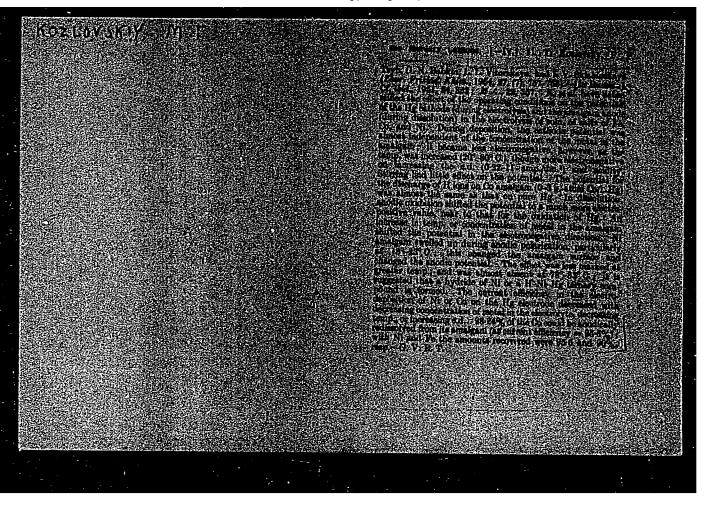
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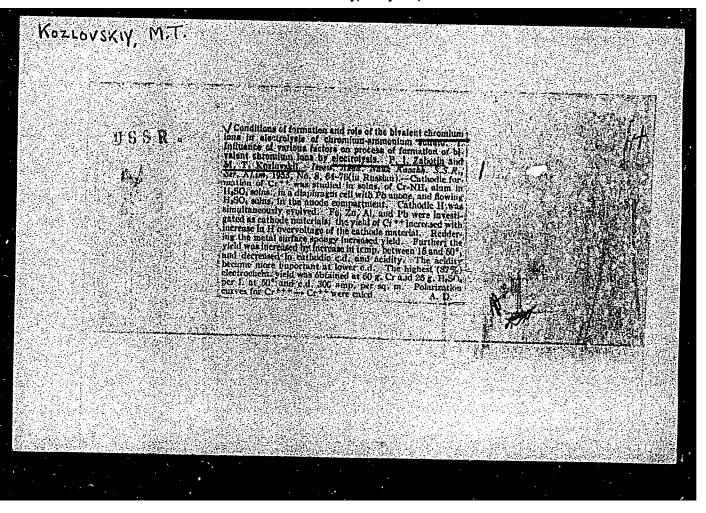
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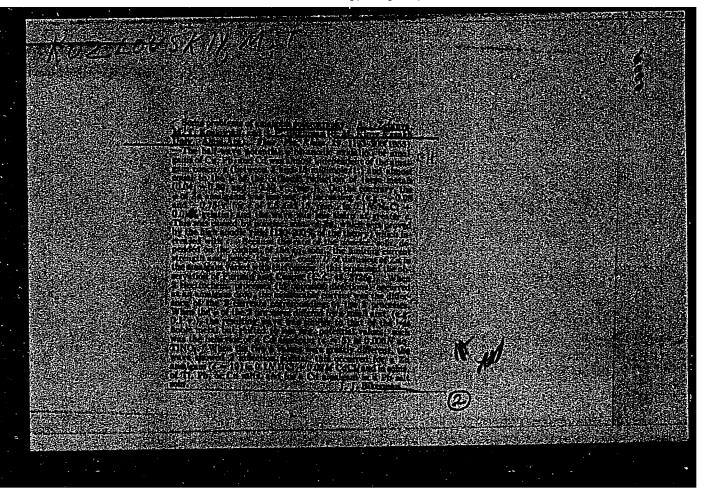
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(Mercury) (Amalgams) (Electrochemistry)